

Product Overview

NTD4809N: Power MOSFET 30V 58A 9 mOhm Single N-Channel DPAK

For complete documentation, see the data sheet

Power MOSFET 30 V, 58 A, Single N-Channel, DPAK/IPAK

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb-Free Devices

Applications

- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	$V_{GS}^{(Max)}$ (V)	$V_{GS}^{(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTD4809NT4G	Pb-free Halide free	Active	N-Channel	Single	30	20	2.5	58	52	14	9	11	25	5	9.2	1456	315	200	DPAK-3	

For more information please contact your local sales support at www.onsemi.com

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